EE566 Solid State Devices

Spring 2005
Dept of Electrical Engineering
University of Notre Dame
Instructor: Debdeep Jena (djena@nd.edu, x8835)

Assignment 5

Posted: 02/21/2005
Due: 02/28/2005

Reading
Chapter 5 of Muller/Kamins/Chan **(MKC).**

Problem 1[1] (Currents in long-base p-n junction - practice)
Problem 5.11, **MKC**.

Problem 2 (Long and Short base p-n junction currents)
We will henceforth call the heavily doped side of an asymmetrical p-n junction as the *EMITTER*, and the lightly doped side the *BASE*, to prepare for the jargon used in bipolar transistors. Consider an ideal n^+-p junction made of GaAs (N_D=2.10^{17}/cm^3, N_A=10^{15}/cm^3) at 300K. Assume that the minority carrier lifetime of electrons in the p-side and holes in the n-side is $\tau_n=\tau_p=0.2\mu s$. Look up data sheets for anything else you might need.

a) Calculate the saturation current density J_0 for the diode (current density is $J= J_0[\exp(V/V_{th})-1]$).

b) *Sketch* the minority and majority carrier profiles outside the depletion region at zero bias, and at a forward bias of V=0.5Volt. Label length scales (diffusion lengths, etc).

c) Calculate and *sketch* the electron and hole current components (both diffusion and recombination) outside the depletion region as a function of distance at this forward bias. Which carriers (minority or majority) dominate the current flow on each side of the junction?

d) Redo parts a) to c) for a *short-base* diode, with the *total* base width (thickness of the p-side) W_B=2μm. Verify that $W_B<<L_n$, where L_n is the minority carrier diffusion length in the base. Make reasonable approximations (linearize slow exponentials, etc) to simplify the problem.

e) Finally, what we are waiting for – when is the current larger – for long base or short base? Can you explain intuitively why this must be so?

Problem 3 (Generation-recombination currents)
Problem 5.10, **MKC**.

Problem 4 (Heterojunction currents)
Instead of a homojunction diode, let us see what happens if a heterojunction is used as the emitter. The doping density in a GaAs based heterostructure p-n junction is N_D=10^{17}/cm^3 and N_A=10^{16}/cm^3. Design the emitter-base junction by introducing $Al_xGa_{1-x}As$ in the emitter layer, such that the total current in the diode improves by a factor of η=100 than the normal GaAs p-n junction. Work out the following -

a) Solve the zero-bias p-n junction problem and determine the depletion thicknesses on both sides.

b) Design your emitter layer such that there are no spikes that impede the current flow. Make generous use of 1D Poisson.

c) Explain why the depletion-edge in the emitter should encompass the whole change in the bandgap, ΔE_G.

d) What are the advantages of the heterojunction over the homojunction? What are the disadvantages?

---

[1] Remember to use proper units and label every figure/plot. Use natural scales such as nm for length, KV/cm for electric fields, and eV for energies. Turn in your answers worked out neatly. Please attach this question sheet to your solution when you turn it in.